

Advanced PECVD-Oxide (HF n=1.46, dep.rate=25.0 nm/min)			
SiO2 depostion~1000A			
Step	SiO2 Deposition		
1	Name	Value	Changeable
	Process pressure	800	N
	RF point	30	N
	stabilization time	15	N
	step time(m)	3	Y
	step time(s)	30	Y
	2%SiH4 %He	600	N
	N2O	1420	N